



**Shinichi Takagi**

**Shinichi Takagi** received the B.S., M.S. and Ph.D. degrees in electronic engineering from the University of Tokyo, Tokyo, Japan, in 1982, 1984 and 1987, respectively. He joined the Toshiba Research and Development Center, Kawasaki, Japan, in 1987, where he has been engaged in the research on the device physics of Si MOSFETs. From 1993 to 1995, he was a Visiting Scholar at Stanford University, Stanford, CA. He worked for the MIRAI Project as the leader of New Transistor Structures and Measurement/Analysis Technology Group from 2001 to 2007. In October 2003, he moved to the University of Tokyo, where he is currently working as a professor in the Department of Electrical Engineering and Information Systems, School of Engineering. His recent interests include the science and the technologies of advanced CMOS devices using new channel materials such as strained-Si, Ge and III-Vs.